Raymond T Tung

List of Publications by Year in descending order

20 papers	2,927 citations	840776 11 h-index	794594 19 g-index
20 all docs	20 docs citations	20 times ranked	3907 citing authors

#	Article	IF	Citations
1	Quantitative explanation of the Schottky barrier height. Physical Review B, 2021, 103, .	3.2	10
2	Fermi level pinning for zinc-blende semiconductors explained with interface bonds. Physical Review B, 2021, 103, .	3.2	7
3	From NiSi2 experiments to density functional theory calculations: How the Schottky barrier mystery was solved. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	1
4	Bulklike band-offset mystery solved through energy minimization: Lessons from perovskite oxide heterojunctions. Physical Review B, 2019, 99, .	3.2	8
5	Charge Density and Band Offsets at Heterovalent Semiconductor Interfaces. Advanced Theory and Simulations, 2018, 1, 1700001.	2.8	20
6	Band offset formation at semiconductor heterojunctions through density-based minimization of interface energy. Physical Review B, 2016, 94, .	3.2	17
7	The physics and chemistry of the Schottky barrier height. Applied Physics Reviews, 2014, 1, .	11.3	931
8	Schottky barrier height systematics studied by partisan interlayer. Thin Solid Films, 2014, 557, 254-257.	1.8	10
9	Effect of metal interaction on the Schottky barrier height on adsorbate-terminated silicon surfaces. Applied Surface Science, 2013, 284, 720-725.	6.1	11
10	Modification of Schottky barrier height on Si (111) by Ga-termination. Surface Science, 2013, 610, 48-52.	1.9	7
11	Inhomogeneous ohmic contacts: Barrier height and contact area determination. Applied Physics Letters, 2012, 101, 051604.	3.3	12
12	Controlled modification of Schottky barrier height by partisan interlayer. Solid State Communications, 2011, 151, 1641-1644.	1.9	14
13	Bidirectional Control of Siliconâ€™s Surface Potential by Means of Molecular Coverage. Journal of Physical Chemistry C, 2010, 114, 18674-18678.	3.1	9
14	Tuning the Electrical Properties of Si Nanowire Fieldâ€Effect Transistors by Molecular Engineering. Small, 2009, 5, 2761-2769.	10.0	80
15	Controlling Au/n-GaAs junctions by partial molecular monolayers. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 3438-3451.	1.8	26
16	Controlling Semiconductor/Metal Junction Barriers by Incomplete, Nonideal Molecular Monolayers. Journal of the American Chemical Society, 2006, 128, 6854-6869.	13.7	102
17	Combined UHV and Liquid Phase (CULP) Processing of Self-assembled Nanostructures. Materials Research Society Symposia Proceedings, 2005, 879, 1.	0.1	0
18	Formation of an electric dipole at metal-semiconductor interfaces. Physical Review B, 2001, 64, .	3.2	275

#	Article	IF	Citations
19	Recent advances in Schottky barrier concepts. Materials Science and Engineering Reports, 2001, 35, 1-138.	31.8	1,041
20	Chemical Bonding and Fermi Level Pinning at Metal-Semiconductor Interfaces. Physical Review Letters, 2000, 84, 6078-6081.	7.8	346